The characterization of different n-type semiconductors and their device application

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ZnO and TiO<sub>2</sub> are the most commonly used n-type semiconductors in various state-of-the-art photovoltaics. Both of materials have similar wide band gap energy approximately 3.2eV. While the TiO<sub>2</sub> has a higher chemical stability and fewer defect states, less recombination, the ZnO have higher electrical conductivity and electron mobility than TiO<sub>2</sub> and can be easily controlled shapes and sizes. The structure, optical and electrical characteristics of ZnO and TiO<sub>2</sub> nanoparticles have been investigated by HR-TEM, FE-SEM, X-ray diffraction, and UV-Vis absorption spectroscopy. In this work, we utilized ZnO and TiO<sub>2</sub> as electron transport materials in solar cells and compared their device performance.